EIC3439-4

ISSUED DATED: 11/12/2007

3.40-3.90GHz 4-Watt Internally Matched Power FET

FEATURES

- **3.40–3.90GHz Bandwidth**
- **Input/Output Impedance Matched to 50 Ohms**
- **+36.5 dBm Output Power at 1dB Compression**
- **12.0 dB Power Gain at 1dB Compression**
- **35% Power Added Efficiency**
- **-46 dBc IM3 at PO = 25.5 dBm SCL**
- **100% Tested for DC, RF, and R_{TH}**

Caution! ESD sensitive device.

ELECTRICAL CHARACTERISTICS (T_a = 25°C)

SYMBOL	PARAMETERS/TEST CONDITIONS[1]	MIN	TYP	MAX	UNITS
P_{1dB}	Output Power at 1dB Compression f = 3.40-3.90GHz V_{DS} = 10 V, I_{DSQ} ≈ 1100mA	35.5	36.5		dBm
G_{1dB}	Gain at 1dB Compression f = 3.40-3.90GHz V_{DS} = 10 V, I_{DSQ} ≈ 1100mA	11.0	12.0		dB
ΔG	Gain Flatness f = 3.40-3.90GHz V_{DS} = 10 V, I_{DSQ} ≈ 1100mA			±0.6	dB
PAE	Power Added Efficiency at 1dB Compression V_{DS} = 10 V, I_{DSQ} ≈ 1100mA f = 3.40-3.90GHz		35		%
Id_{1dB}	Drain Current at 1dB Compression f = 3.40-3.90GHz		1200	1500	mA
IM3	Output 3rd Order Intermodulation Distortion Δf = 10 MHz 2-Tone Test; Pout = 25.5 dBm S.C.L[2] V_{DS} = 10 V, I_{DSQ} ≈ 65% IDSS f = 3.90GHz	-43	-46		dBc
I_{DSS}	Saturated Drain Current V_{DS} = 3 V, V_{GS} = 0 V		2000	2500	mA
V_P	Pinch-off Voltage V_{DS} = 3 V, I_{DS} = 20 mA		-2.5	-4.0	V
R_{TH}	Thermal Resistance[3]		5.5	6.0	°C/W

Note: 1. Tested with 100 Ohm gate resistor.
2. S.C.L. = Single Carrier Level.
3. Overall Rth depends on case mounting.

ABSOLUTE MAXIMUM RATING FOR EFE

SYMBOLS	PARAMETERS	ABSOLUTE[1]	CONTINUOUS[2]
V_{DS}	Drain-Source Voltage	15V	10V
V_{GS}	Gate-Source Voltage	-5V	-4V
Igsf	Forward Gate Current	48.0 mA	14.4 mA
Igsr	Reverse Gate Current	-9.6 mA	-2.4 mA
Pin	Input Power	35.5dBm	@ 3dB Compression
Tch	Channel Temperature	175 °C	175 °C
Tstg	Storage Temperature	-65 to +175 °C	-65 to +175 °C
Pt	Total Power Dissipation	25W	25W

Note: 1. Exceeding any of the above ratings may result in permanent damage.
2. Exceeding any of the above ratings may reduce MTTF below design goals.

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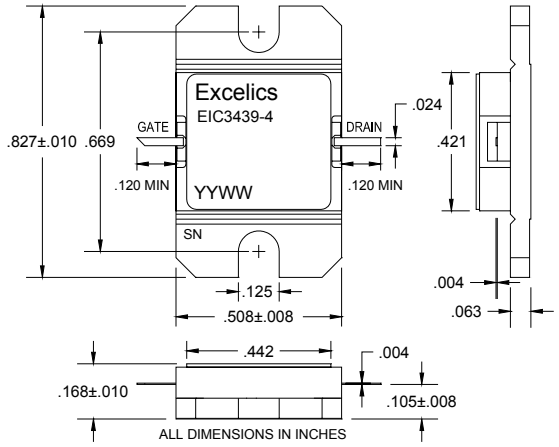
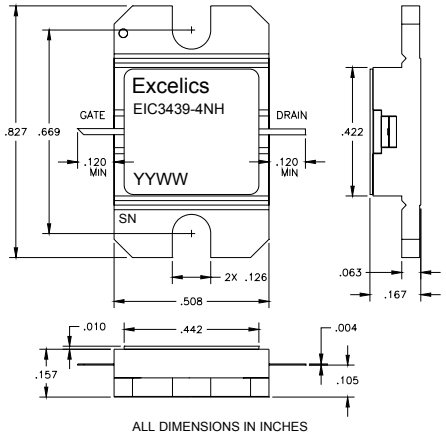
PACKAGES OUTLINE

Dimensions in inches, Tolerance ± .005 unless otherwise specified

EIC3439-4 (Hermetic)



EIC3439-4NH (Non-Hermetic)



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ORDERING INFORMATION

Part Number	Packages	Grade[1]	f_{Test} (GHz)	P_{1dB} (min)	IM_3 (min)[2]
EIC3439-4	Hermetic	Industrial	3.40-3.90GHz	35.5	-43
EIC3439-4NH	Non-Hermetic	Industrial	3.40-3.90GHz	35.5	-43

Notes: 1. Contact factory for military and hi-rel grades.
2. Exact test conditions are specified in “Electrical Characteristics” table.

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